L Number	Hits	Search Text	DB	Time stamp
3	0	20040016963.URPN.	USPAT	2004/03/10 15:57
6	0	20020177285.URPN.	USPAT	2004/03/10 16:05
9	0	20020036319.URPN.	USPAT	2004/03/10 16:08
13	1	6545316.URPN.	USPAT	2004/03/10 16:14
17	2	6174773.URPN.	USPAT	2004/03/10 16:17
19	130	"base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 16:26
20	103	(vertical adj MOSFET) and "drift region" and trench	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 16:27
21	87	("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 16:27
22	11	(("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench"	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 16:28
23	1457	438/197	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:00
26	0	438/197 and base and drift and trench and P/N	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:00
25	2	438/197 and base and drift and trench and P-N	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:01
27	7	438/197 and base and drift and trench and PN	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:04
28	328	438/212	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:03
29	1	438/212 and base and drift and trench and P/N	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:03

31	10	438/212 and base and drift and trench and P-N	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:05
32	3	(438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:04
33	894	438/268	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:08
34	2	438/268 and base and drift and trench and P/N	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:08
35	8	438/212 and base and drift and trench and PN	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:09
36	3	(438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:05
37	18	438/268 and base and drift and trench and P-N	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:09
38	9	(438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:07
39	27	438/268 and base and drift and trench and PN	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:07

40	15	(438/268 and base and drift and trench and PN) not (438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:09
41	1043	438/270	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:08
42	2	438/270 and base and drift and trench and P/N	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:08
43	21	438/270 and base and drift and trench and PN	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:09
44	20	438/270 and base and drift and trench and P-N	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:09
45	5	(438/270 and base and drift and trench and PN) not (438/268 and base and drift and trench and PN) not (438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:10
47	3	(438/270 and base and drift and trench and P-N) not (438/270 and base and drift and trench and PN) not (438/268 and base and drift and trench and PN) not (438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:11

48	0	(438/270 and base and drift and trench and P/N) not (438/270 and base and drift and trench and P-N) not (438/270 and base and drift and trench and PN) not (438/268 and base and drift and trench and PN) not (438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:17
49	71	UMOSFET and drift and base	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:11
50	36	(UMOSFET and drift and base) not (438/270 and base and drift and trench and P-N) not (438/270 and base and drift and trench and PN) not (438/268 and base and drift and trench and PN) not (438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:15
51	353	power and MOSFET and drift and (surface adj4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 17:17
52	211	(power and MOSFET and drift and (surface adj4 electrode)) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 17:17
53	139	((power and MOSFET and drift and (surface adj4 electrode)) and trench) and (PN or P/N or P-N)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 17:17

54	71	(((power and MOSFET and drift and (surface adj4 electrode)) and trench) and (PN or P/N or P-N)) not (438/270 and base and drift and trench and P/N) not (438/270 and base and drift and trench and P-N) not (438/270 and base and drift and trench and PN) not (438/268 and base and drift and trench and PN) not (438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:23
55	25	((((power and MOSFET and drift and (surface adj4 electrode)) and trench) and (PN or P/N or P-N)) not (438/270 and base and drift and trench and P/N) not (438/270 and base and drift and trench and P-N) not (438/270 and base and drift and trench and PN) not (438/268 and base and drift and trench and PN) not (438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)) and deep	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:18
56	80	"vertical MOSFET" and drift and (PN or P/N or P-N) and base and trench	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:23
57	6	("vertical MOSFET" and drift and (PN or P/N or P-N) and base and trench) not (((power and MOSFET and drift and (surface adj4 electrode)) and trench) and (PN or P/N or P-N)) not (438/270 and base and drift and trench and P/N) not (438/270 and base and drift and trench and P-N) not (438/270 and base and drift and trench and PN) not (438/268 and base and drift and trench and PN) not (438/268 and base and drift and trench and P-N) not (438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not (438/212 and base and drift and trench and P/N) not (438/197 and base and drift and trench and PN) not (438/197 and base and drift and trench and P-N) not ((("base region" and "drift region" and trench and ("P/N junction" or "P-N junction" or "PN junction" or "P N junction")) not ((vertical adj MOSFET) and "drift region" and trench)) and "deep trench") not ((vertical adj MOSFET) and "drift region" and trench)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 17:23

-	2	5912497.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 11:06
-	103	(vertical adj MOSFET) and "drift region" and trench	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 16:27
-	2	6388286.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 15:23
-	3	6452230.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 15:21
-	2	5756386.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 15:23
-	2	5962893.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 15:22
-	2	6091108.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 15:24
-	2	5177572.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 15:25
-	2	5831288.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 15:26
-	2	5412241.pn.	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/08 15:26
-	103	(vertical adj MOSFET) and "drift region" and trench	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2004/03/10 16:23